



1W 405nm Laser Diode

Absolute maximum ratings (Tc=25°C)

Item	Symbol	Ratings	Unit
Optical output power	Po	1,100	mW
LD Reverse Voltage	V _{R(LD)}	2	V
Operating Temperature	Topr	0 ~ +30	°C
Storage Temperature	Tstg	-40 ~ +85	°C

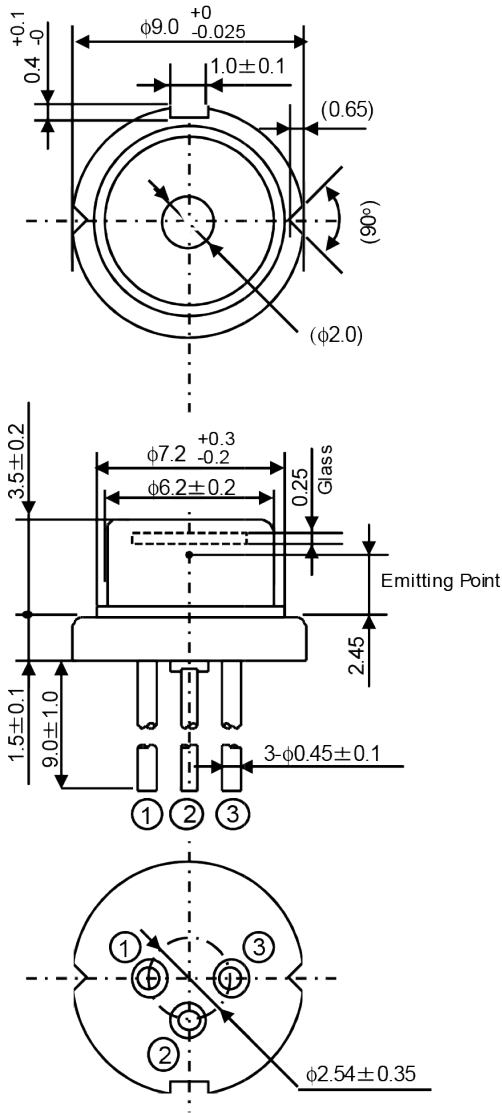
Optical and Electrical Characteristics (Tc=25°C)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Threshold current	I _{th}	250	320	400	mA	-
Operating current	I _{op}	-	1,000	1,300	mA	Po=1,000mW
Operating voltage	V _{op}	-	-	5.0	V	Po=1,000mW
Beam divergence Parallel to the junction	θ _{//}	5	13	25	°	Po=1,000mW, Full angle 1/e ²
Beam divergence Perpendicular to the junction	θ	30	42	50	°	Po=1,000mW, Full angle 1/e ²
Lasing Wavelength	λ _p	400	405	410	nm	Po=1,000mW



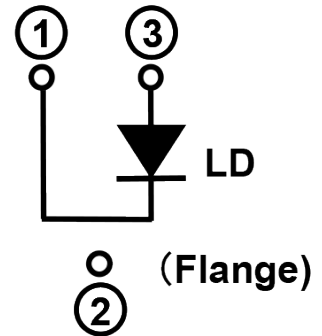
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Outline



(Unit: mm)

Internal Circuit





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Typical Characteristic Curves

